

isc Silicon PNP Power Transistor

2SB762

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= -60V(Min)
- · Good Linearity of hFE
- Wide Area of Safe Operation
- Complement to Type 2SD857
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

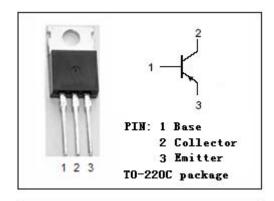


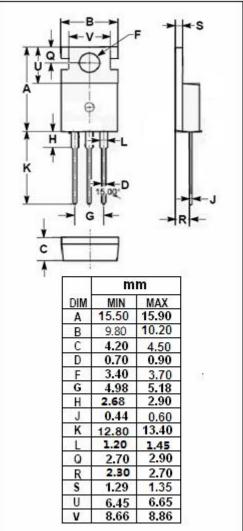
APPLICATIONS

· Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	-60	V	
V _{CEO}	Collector-Emitter Voltage	Voltage -60		
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current-Continuous	-4	Α	
Ісм	Collector Current-Peak	-8	Α	
Pc	Collector Power Dissipation @ T_c =25 $^{\circ}$ C	40	W	
TJ	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range	nge -55~150		







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-60			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	Ic= -3A; Vc== -4V			-2.0	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -30V; I _B = 0			-700	μА
Ices	Collector Cutoff Current	V _{CE} = -60V; V _{BE} = 0			-400	μА
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-7	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -4V	40		250	
h _{FE-2}	DC Current Gain	I _C = -3A; V _{CE} = -4V	15			

♦ h_{FE-1} Classifications

R	Q	Р
40-90	70-150	120-250

NOTICE:

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